

P-Channel Enhancement Mode Power MOSFET

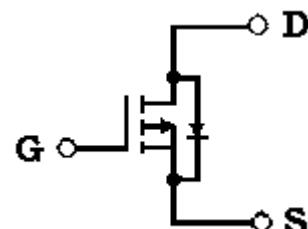
TO-252(DPAK)

Features:

- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating & Halogen-free package



BV _{DSS}	-60V
I _D @ V _{GS} =-10V, T _C =25°C	-17A
R _{DSON} @V _{GS} =-10V, I _D =-15A	64mΩ (typ.)
R _{DSON} @V _{GS} =-4.5V, I _D =-7A	68 mΩ (typ.)



G : Gate D : Drain
S : Source

Ordering Information

Device	Package	Shipping
KJB40P06	TO-252 (Pb-free lead plating & Halogen-free package)	2500 pcs / Tape & Reel

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current @ $V_{GS}=-10\text{V}$, $T_c=25^\circ\text{C}$	I_D	-17	A
Continuous Drain Current @ $V_{GS}=-10\text{V}$, $T_c=100^\circ\text{C}$		-11	
Pulsed Drain Current *1	I_{DM}	-60	A
Avalanche Current	I_{AS}	-12	
Avalanche Energy @ $L=0.1\text{mH}$, $I_D=-12\text{A}$, $R_G=25\Omega$	E_{AS}	7.2	mJ
Repetitive Avalanche Energy @ $L=0.05\text{mH}$ *2	E_{AR}	3.6	
Total Power Dissipation @ $T_c=25^\circ\text{C}$	P_D	33	W
Total Power Dissipation @ $T_c=100^\circ\text{C}$		16.5	
Operating Junction and Storage Temperature Range	T_J , T_{stg}	-55~+175	$^\circ\text{C}$

Note : *1. Pulse width limited by maximum junction temperature

*2. Duty cycle $\leq 1\%$

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{\theta JC}$	4.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{\theta JA}$	110	

Characteristics ($T_c=25^\circ\text{C}$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	-60	-	-	V	$V_{GS}=0\text{V}$, $I_D=-250\mu\text{A}$
$V_{GS(\text{th})}$	-1	-	-3		$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$
I_{GSS}	-	-	± 100	$n\text{A}$	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$
ID_{SS}	-	-	-1	μA	$V_{DS}=-48\text{V}$, $V_{GS}=0\text{V}$
	-	-	-25		$V_{DS}=-40\text{V}$, $V_{GS}=0\text{V}$, $T_J=125^\circ\text{C}$
$I_{D(\text{ON})}$ *1	-17	-	-	A	$V_{DS}=-5\text{V}$, $V_{GS}=-4.5\text{V}$
$R_{DS(\text{ON})}$ *1	-	64	80	$\text{m}\Omega$	$V_{GS}=-10\text{V}$, $I_D=-15\text{A}$
	-	68	90		$V_{GS}=-4.5\text{V}$, $I_D=-7\text{A}$
G_{FS} *1	-	12	-	S	$V_{DS}=-5\text{V}$, $I_D=-15\text{A}$
Dynamic					
Q_g *1, 2	-	26.2	-	nC	$V_{DS}=-30\text{V}$, $I_D=-10\text{A}$, $V_{GS}=-10\text{V}$
Q_{gs} *1, 2	-	3.8	-		
Q_{gd} *1, 2	-	4.3	-		
$t_{d(\text{ON})}$ *1, 2	-	5.8	-	ns	$V_{DS}=-30\text{V}$, $I_D=-1\text{A}$, $V_{GS}=-10\text{V}$, $R_G=6\Omega$
t_r *1, 2	-	7.2	-		
$t_{d(\text{OFF})}$ *1, 2	-	140	-		
t_f *1, 2	-	91	-		

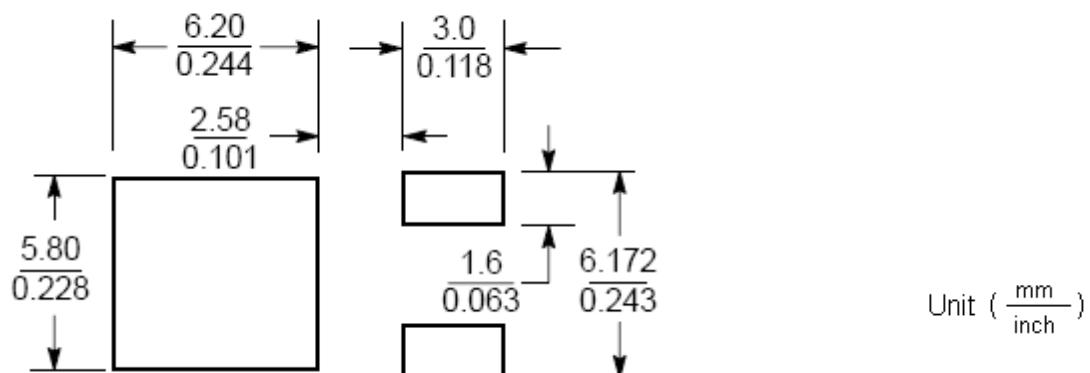
C _{iss}	-	1414	-	pF	V _{GS} =0V, V _{DS} =-25V, f=1MHz
C _{oss}	-	68	-		
C _{rss}	-	55	-		
R _g	-	33	-	Ω	V _{GS} =15mV, V _{DS} =0V, f=1MHz
Source-Drain Diode Ratings and Characteristics					
I _s *1	-	-	-17	A	
I _{SM} *3	-	-	-60		
V _{SD} *1	-	-	-1.3	V	I _F =I _s , V _{GS} =0V
t _{rr}	-	12	-	ns	I _F =-5A, dI _F /dt=100A/μs
Q _{rr}	-	9	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

*2.Independent of operating temperature

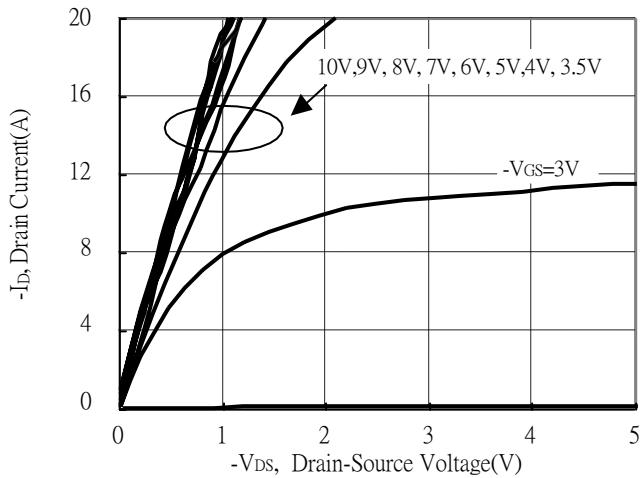
*3.Pulse width limited by maximum junction temperature.

Recommended soldering footprint

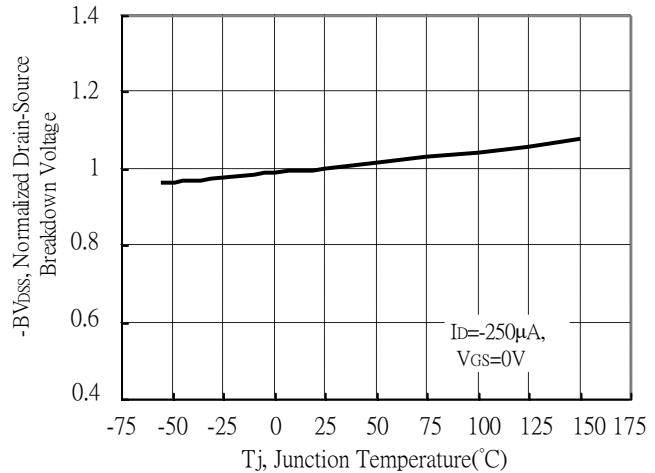


Typical Characteristics

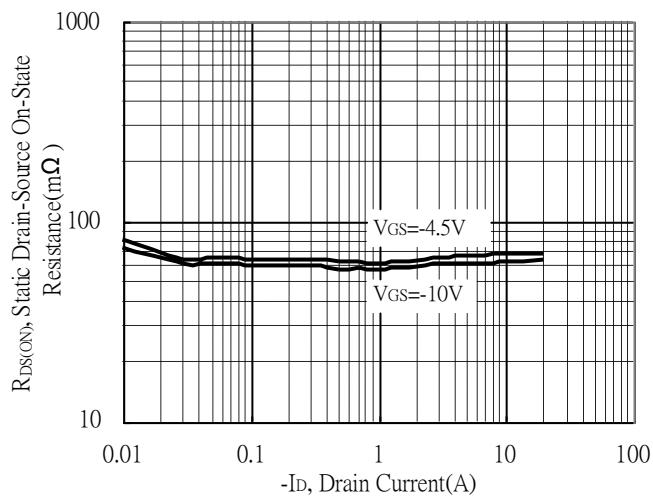
Typical Output Characteristics



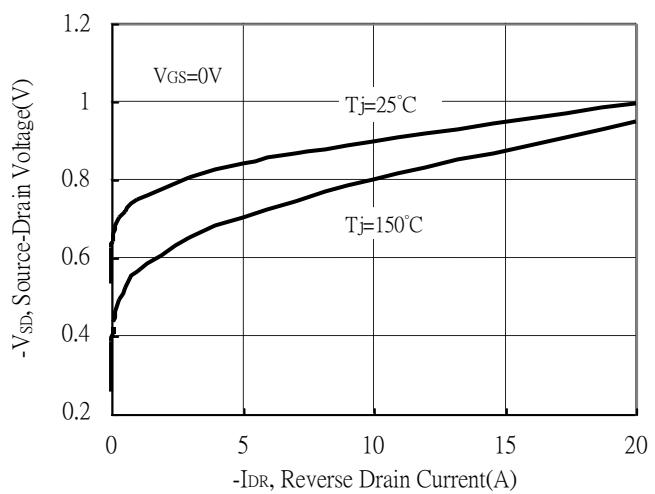
Breakdown Voltage vs Ambient Temperature



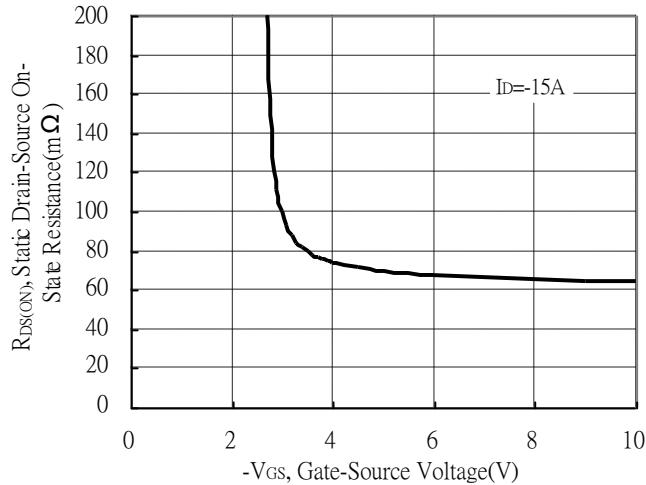
Static Drain-Source On-State resistance vs Drain Current



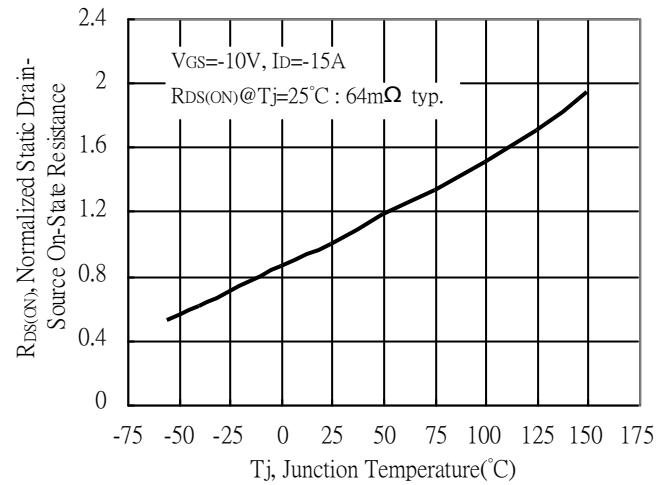
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

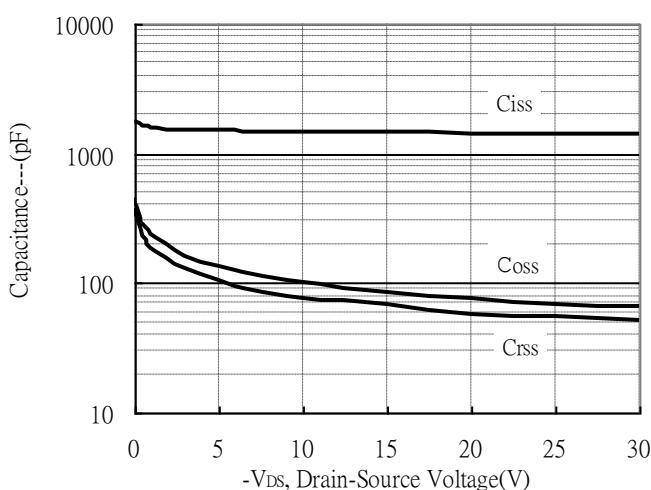


Drain-Source On-State Resistance vs Junction Temperature

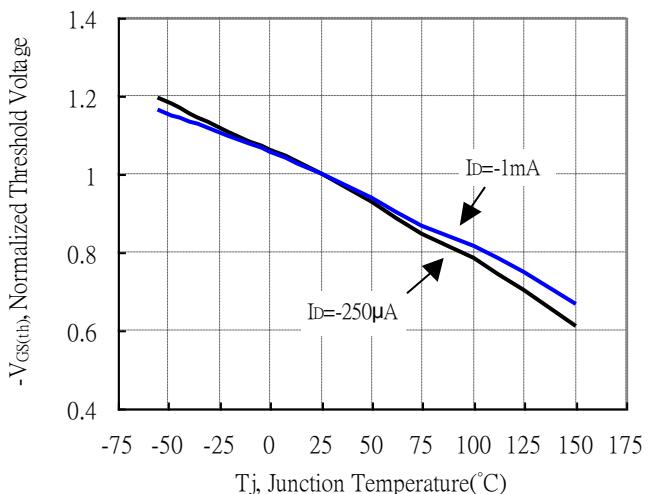


Typical Characteristics (Cont.)

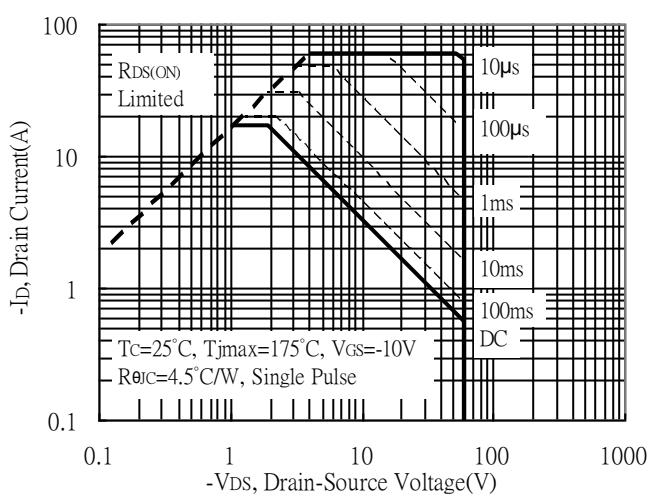
Capacitance vs Drain-to-Source Voltage



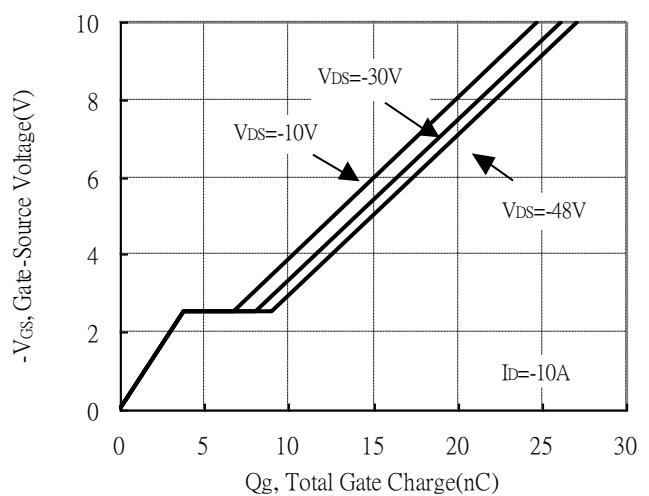
Threshold Voltage vs Junction Temperature



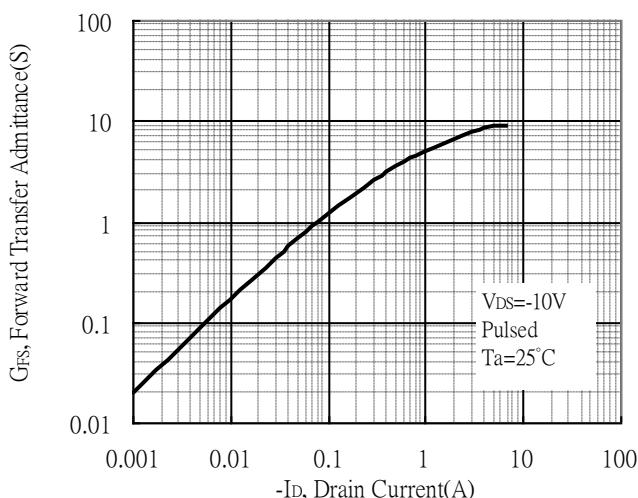
Maximum Safe Operating Area



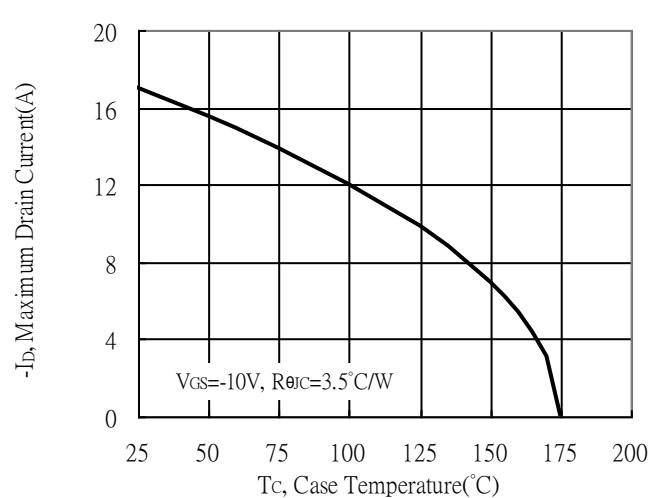
Gate Charge Characteristics



Forward Transfer Admittance vs Drain Current

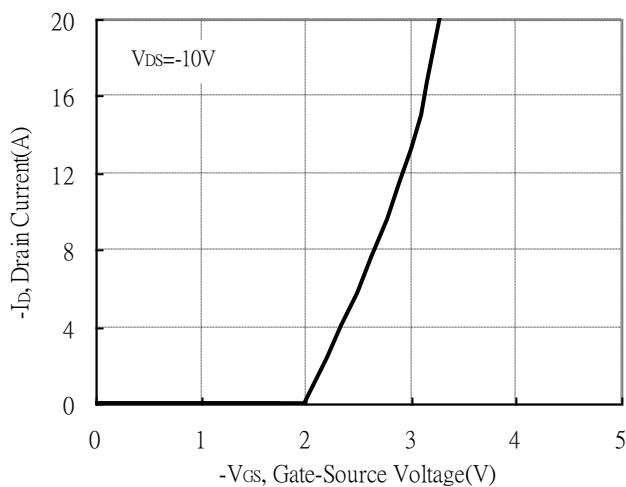


Maximum Drain Current vs Case Temperature

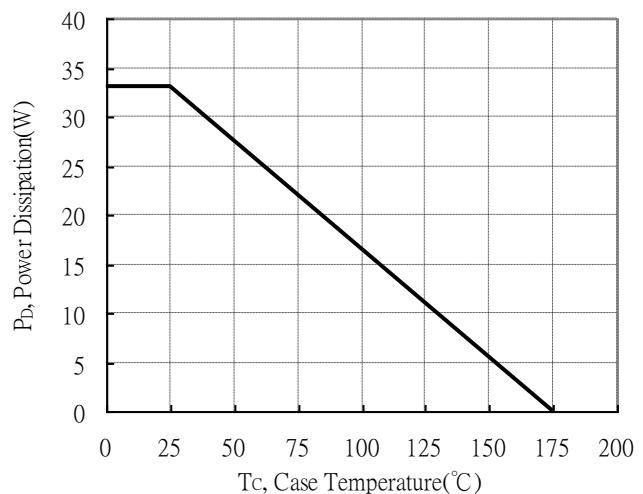


Typical Characteristics (Cont.)

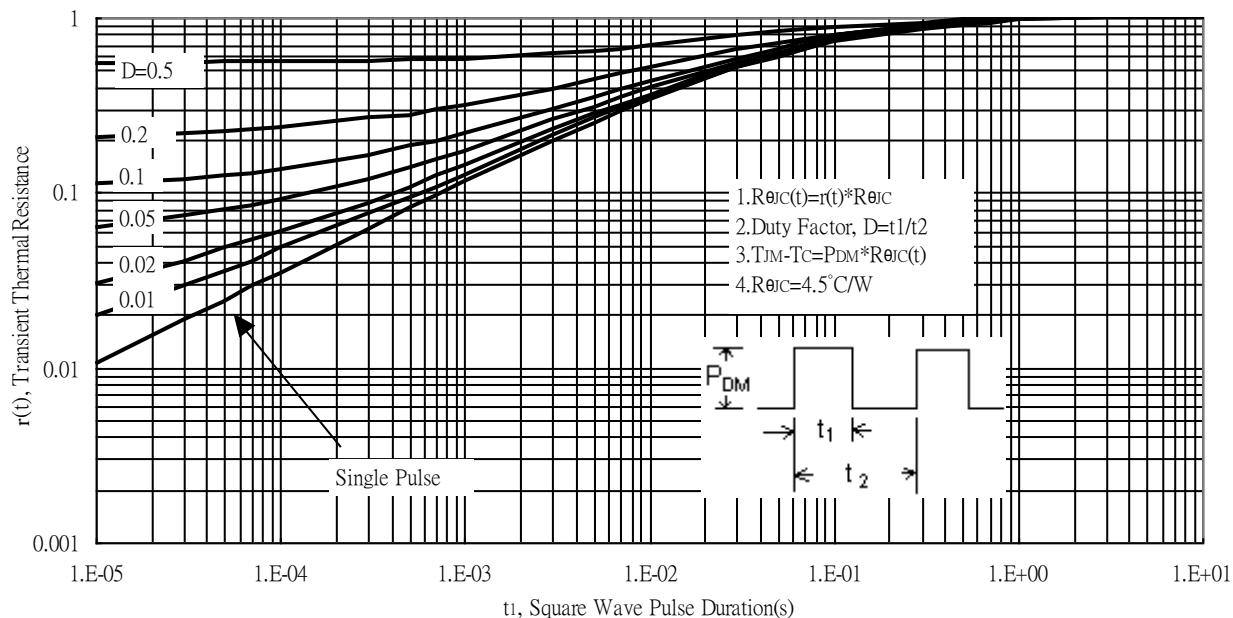
Typical Transfer Characteristics



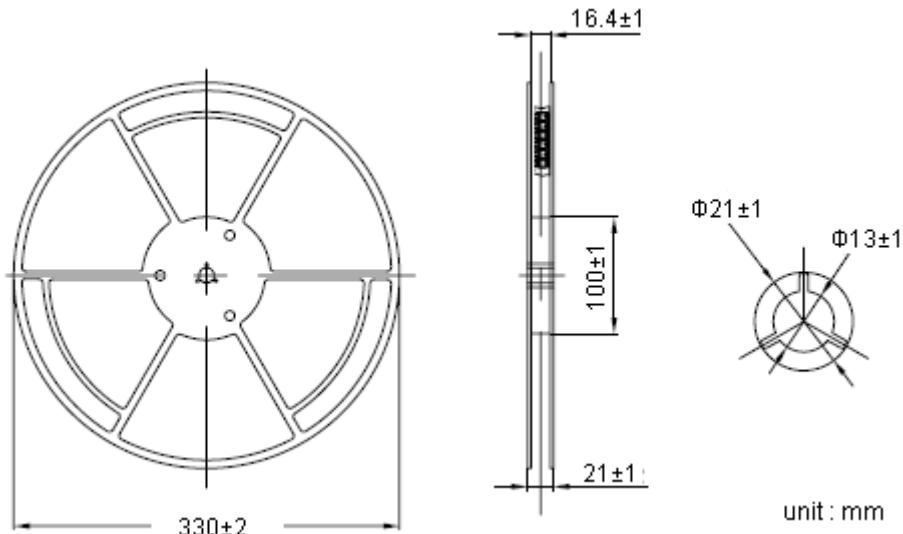
Power Derating Curve



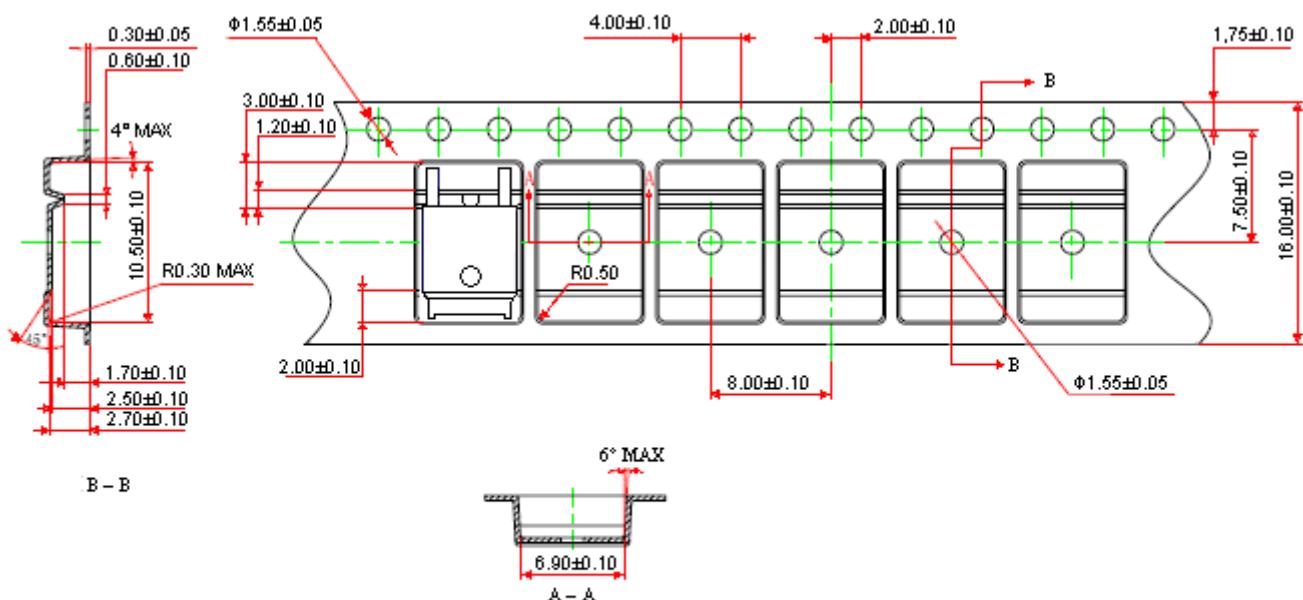
Transient Thermal Response Curves



Reel Dimension



Carrier Tape Dimension

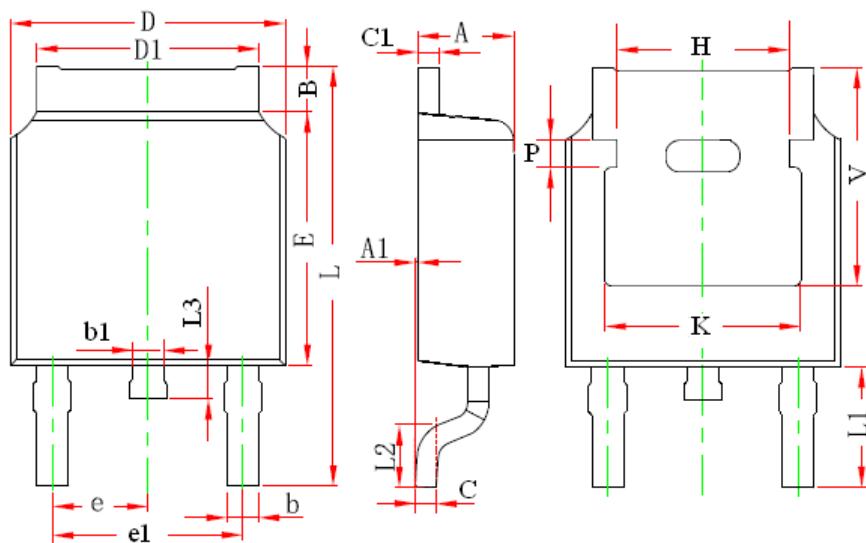


Notes:

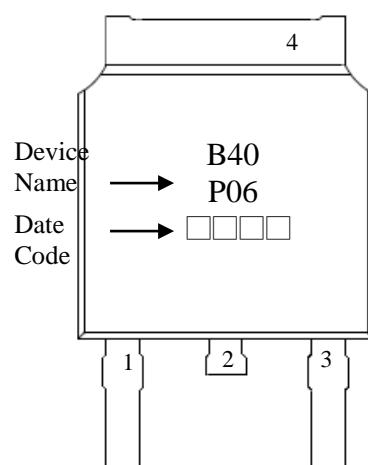
1. 10 sprocket hole pitch cumulative tolerance ± 0.2 .
2. Camber not to exceed 1mm in 100mm.
3. Material: conductive black polystyrene, antistatic coated : $10^5 \Omega/\square \sim 10^{11} \Omega/\square$

unit : mm

TO-252 Dimension



Marking:



3-Lead TO-252 Plastic Surface Mount Package

Style: Pin 1.Gate 2.Drain 3.Source
4.Drain

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF